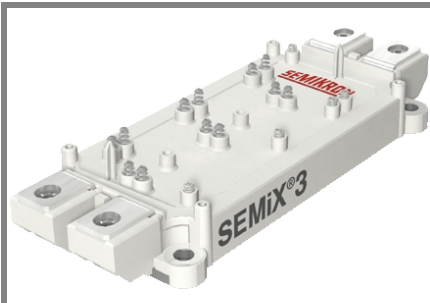


SEMiX 703GB126HDs



SEMiX® 3s

Trench IGBT Modules

SEMiX 703GAL126HDs

SEMiX 703GAR126HDs

SEMiX 703GB126HDs

Preliminary Data

Features

- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability

Typical Applications

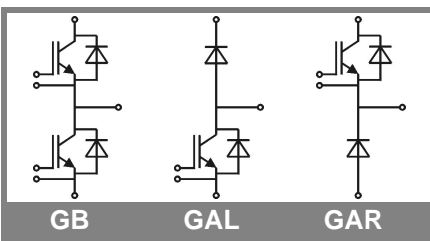
- AC inverter drives
- UPS
- Electronic Welding

Remarks

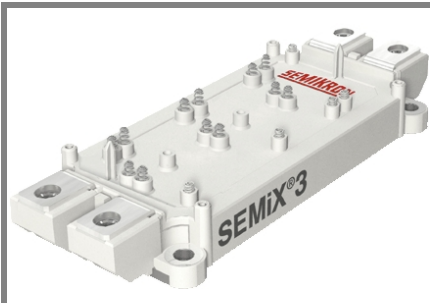
- Case temperatur limited to $T_C = 125^\circ\text{C}$ max.

Absolute Maximum Ratings		$T_{case} = 25^\circ\text{C}$, unless otherwise specified		
Symbol	Conditions	Values	Units	
IGBT				
V_{CES}	$T_j = 25^\circ\text{C}$	1200	V	
I_C	$T_j = 150^\circ\text{C}$	$T_c = 25^\circ\text{C}$	700	A
		$T_c = 80^\circ\text{C}$	490	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	900	A	
V_{GES}		± 20	V	
t_{psc}	$V_{CC} = 600\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125^\circ\text{C}$ $V_{CES} < 1200\text{ V}$	10	μs	
Inverse Diode				
I_F	$T_j = 150^\circ\text{C}$	$T_c = 25^\circ\text{C}$	560	A
		$T_c = 80^\circ\text{C}$	380	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	900	A	
I_{FSM}	$t_p = 10\text{ ms}; \text{sin.}$	$T_j = 25^\circ\text{C}$	2900	A
Module				
$I_{t(RMS)}$		600	A	
T_{vj}		- 40 ... + 150	$^\circ\text{C}$	
T_{stg}		- 40 ... + 125	$^\circ\text{C}$	
V_{isol}	AC, 1 min.	4000	V	

Characteristics		$T_{case} = 25^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 12\text{ mA}$	5	5,8	6,5	V
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$			0,6	mA
V_{CE0}		$T_j = 25^\circ\text{C}$	1	1,2	V
		$T_j = 125^\circ\text{C}$	0,9	1,1	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	1,45	2	$\text{m}\Omega$
		$T_j = 125^\circ\text{C}$	2,45	2,9	$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 450\text{ A}, V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}_{chiplev.}$	1,7	2,15	V
		$T_j = 125^\circ\text{C}_{chiplev.}$	2	2,45	V
C_{res}	$V_{CE} = 25, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	33		nF
C_{oes}			1,7		nF
C_{res}			1,5		nF
$t_{d(on)}$	$R_{Gon} = 1,6\ \Omega$	$V_{CC} = 600\text{ V}$ $I_{Cnom} = 450\text{ A}$	310		ns
t_r			60		ns
E_{on}	$R_{Goff} = 1,6\ \Omega$	$T_j = 125^\circ\text{C}$	32		mJ
$t_{d(off)}$			680		ns
t_f			135		ns
E_{off}			68		mJ
$R_{th(j-c)}$	per IGBT			0,055	K/W



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Remarks

- Case temperatur limited to $T_C=125^\circ\text{C}$ max.

Characteristics		min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 450 \text{ A}; V_{GE} = 0 \text{ V}$		1,6	1,8	V
	$T_j = 25^\circ\text{C}_{chiplev.}$				
	$T_j = 125^\circ\text{C}_{chiplev.}$		1,6	1,8	V
V_{F0}			1	1,1	V
	$T_j = 25^\circ\text{C}$				
	$T_j = 125^\circ\text{C}$		0,8	0,9	V
r_F			1,3	1,6	mΩ
	$T_j = 25^\circ\text{C}$				
	$T_j = 125^\circ\text{C}$		1,8	2	mΩ
I_{RRM}	$I_{Fnom} = 450 \text{ A}$		580		A
Q_{rr}	$di/dt = 6900 \text{ A}/\mu\text{s}$		130		μC
E_{off}	$V_{GE} = -15 \text{ V}; V_{CC} = 600 \text{ V}$		60		mJ
$R_{th(j-c)D}$	per diode			0,11	K/W
Module					
L_{CE}			20		nH
$R_{CC'+EE'}$	res., terminal-chip	$T_{case} = 25^\circ\text{C}$	0,7		mΩ
		$T_{case} = 125^\circ\text{C}$	1		mΩ
$R_{th(c-s)}$	per module		0,04		K/W
M_s	to heat sink (M5)		3	5	Nm
M_t	to terminals (M6)		2,5	5	Nm
w			290	300	g
Temperature sensor					
R_{100}	$T_c = 100^\circ\text{C}$ ($R_{25} = 5 \text{ k}\Omega$)		0,493±5%		kΩ
$B_{100/125}$	$R(T) = R_{100} \exp[B_{100/125} (1/T - 1/T_{100})]$; $T[\text{K}]; B$		3550±2%		K

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

